

IN THE CLAIMS

Cancel claims 4 to 8. Please amend claims 1-3 as follows:

1. (Twice Amended) A method of forming a CMOS sidewall spacer, comprising the steps of:

forming a PMOS transistor gate structure on a n-type region of a semiconductor substrate;

forming a NMOS transistor gate structure on a p-type region of said semiconductor substrate;

forming initial single layer sidewall structures of similar widths adjacent to said NMOS transistor gate structure and said PMOS transistor gate structure; and

etching said single layer sidewall structure adjacent to said NMOS transistor gate structure such that the width of the single layer sidewall structure adjacent to said NMOS transistor gate structure is less than the width of the single layer sidewall structure adjacent to said PMOS transistor gate structure.

2. (Twice Amended) The method of claim 1 wherein said etching of said initial single layer sidewall structure is an anisotropic etch.

3. (Twice Amended) The method of claim 1 wherein said initial single layer sidewall structure is a material selected from the group consisting of silicon nitride, silicon oxide, and silicon oxynitride.